

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT

APPLICANT(S): Hiroshi Tayanaka ATTORNEY DOCKET NO: P97,0027
SERIAL NO.: 08/818,239 GROUP ART UNIT: 2813
FILING DATE: March 14, 1997 EXAMINER: K. Christiansen
INVENTION: "METHOD FOR MAKING THIN FILM SEMICONDUCTOR,
SOLAR CELL, AND LIGHT EMITTING DIODE"

Hon. Assistant Commissioner for Patents
Washington, DC 20231

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S I R:

In accordance with the provisions of 37 C.F.R. §1.56, Applicant requests that citation and examination of the references identified on the attached PTO-1449 form, copies of which are enclosed herewith accompanied by English-language Derwent abstract, where required, in accordance with 37 C.F.R. §1.98, be made during the course of examination of the above-mentioned application for United States Patent. Except as provided, the undersigned does not possess English translations of the non-English references.

The mailing date of this Information Disclosure Statement is within three months of the filing date of the CPA Request in the present application.

I. SUBMITTED UNITED STATES PATENT REFERENCES

<u>Reference</u>	<u>Patent Number</u>	<u>Patentee</u>	<u>Issue Date</u>
AA	4,727,047	Bozler et al.	Feb. 23, 1988
AB	5,854,123	Sato et al.	Dec. 29, 1998
AC	5,856,229	Sakaguchi et al.	Jan. 5, 1999

II. SUBMITTED FOREIGN PATENT REFERENCES

<u>Reference</u>	<u>Patent Number</u>	<u>Country</u>	<u>Publication Date</u>
AL	62-279625	Japan	Dec. 4, 1987

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III. SUBMITTED PUBLICATIONS

- AR V. Labunov et al., "Heat Treatment Effect on Porous Silicon", Thin Solid Films, Vol. 137, pp. 123-134, 1986.
- AS N. Sato et al., "Epitaxial Growth on Porous Si for a New Bond and Etch-back SOI", The Electrochemical Society, Spring Meeting, May 22-27, 1994, Extended Abstracts, Vol. 94-1, Abstract No. 443, pp. 705-706.
- AT "Crystalline Silicon and Doping", Maruzen Kabushiki Kaisha Publisher, 1986.

II. REMARKS

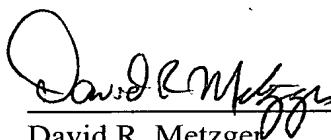
References AA, AB, AC, AL, AR, AS and AT are prior art in the general field of the present invention. Reference AL, which is in Japanese, discloses epitaxial growth forming monocrystal layer on semiconductor. Reference AT is in Japanese, and no English translation is presently available. However, if the Examiner desires such, Applicant will provide it upon request. Since references AA, AB, AC, AR, and AS are in English no further commentary concerning their teachings is necessary.

A copy of an English-language disclosure abstracts for reference AL from Derwent's WPI database is included.

The above references do not disclose or suggest a method for making thin film semiconductor, solar cell or light emitting diode as disclosed in the present invention.

In view of the foregoing, Applicant submits that all claims of the application are patentably distinguishable over the teachings of the above references, taken singly or in combination. Early consideration of the application is, therefore, requested.

Respectfully submitted,



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